

L Number	Hits	Search Text	DB	Time stamp
-	1991	@ad<=20001221 and 'memory' same 'high voltage' same 'logic'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 11:28
-	16	@ad<=20001221 and 'memory' same 'high voltage transistor' same 'logic transistor'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/11 09:03
-	609	@ad<=20001221 and 'memory' with 'high voltage' with 'logic'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/10 16:33
-	488	@ad<=20001221 and (257/314).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 13:54
-	1092	@ad<=20001221 and (257/315).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 13:54
-	148	@ad<=20001221 and (257/326).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/11 09:02
-	1441	@ad<=20001221 and (257/316).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 13:54
-	295	@ad<=20001221 and (257/317).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 13:54
-	188	@ad<=20001221 and (257/318).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 13:55
-	1340	@ad<=20001221 and (438/257-258).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 13:55
-	246	@ad<=20001221 and (438/266).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 13:55
-	92	@ad<=20001221 and (438/242).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 13:55
-	53	@ad<=20001221 and 'memory' and 'HV' adj1 'transistor'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/11 09:22
-	161	@ad<=20001221 and (438/201).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/11 09:17

-	2	("6287907").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/11 09:22
-	2	("6037625").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/11 09:22
-	2	("6197635").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/11 09:23
-	2	("6194270").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/11 09:23
-	2	("5904518").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/11 09:23
-	2	("4719184").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/11 09:23
-	2	("4471373").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/11 09:23
-	256	@ad<=20001221 and (257/315).ccls. and logic and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/11 09:29
-	14959	@ad<=20001221 and logic and memory and 'high voltage'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/11 09:40
-	274	@ad<=20001221 and 'logic' and 'memory cell' and 'high voltage transistor'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/11 09:42
-	44	@ad<=20001221 and 'memory cell' and 'logic transistor' and 'high voltage transistor'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/11 11:06
-	470	@ad<=20001221 and 'memory' and 'high voltage transistor' and 'low voltage'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/11 11:09
-	304	@ad<=20001221 and 'memory cell' and 'high voltage transistor' and 'low voltage'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/11 11:35
-	90	@ad<=20001221 and 'memory cell' same 'high voltage transistor' same 'low voltage'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/11 11:36

-	29	@ad<=20001221 and 'memory cell' and 'HV transistor' and 'LV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 13:57
-	223	@ad<=20001221 and 'memory cell' and 'logic transistor'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/11 14:21
-	2	"20030168694"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 11:28
-	218	@ad<=20001221 and (257/319).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 13:53
-	216	@ad<=20001221 and (257/320).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 13:53
-	738	@ad<=20001221 and (257/321).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 13:54
-	204	@ad<=20001221 and (257/322).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 13:54
-	82	@ad<=20001221 and (257/323).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 13:54
-	454	@ad<=20001221 and (257/324).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 13:55
-	109	@ad<=20001221 and (257/325).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 13:55
-	150	@ad<=20001221 and (257/326).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 13:55
-	498	@ad<=20001221 and (257/314).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 13:55
-	1106	@ad<=20001221 and (257/315).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 13:56
-	1453	@ad<=20001221 and (257/316).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 13:57

-	298	@ad<=20001221 and (257/317).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 13:57
-	193	@ad<=20001221 and (257/318).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 13:58
-	1352	@ad<=20001221 and (438/257-258).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 13:59
-	250	@ad<=20001221 and (438/266).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 13:59
-	94	@ad<=20001221 and (438/242).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 13:59
-	46	@ad<=20001221 and 'memory cell' and 'High voltage transistor' and 'Logic transistor'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 14:00
-	4	((("5793673") or ("5792670")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 14:00
-	2	@ad<=20001221 and 'memory cell' and 'HV' with 'transistor' and 'Logic transistor'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 14:01
-	45	@ad<=20001221 and 'memory cell' and 'HV' with 'transistor' and 'LV' with 'transistor'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 14:01
- - - - -	146	@ad<=20001221 and 'memory cell' and 'high voltage transistor' and 'low voltage transistor'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 16:23
-	362	@ad<=20001221 and 'FLOTOX'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 15:13
-	0	@ad<=20001221 and 'EEPROM' and 'high voltage transistor' and 'low voltage transistor'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 16:24
-	10	@ad<=20001221 and 'EEPROM' and 'high voltage transistor' and 'low voltage transistor'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 16:25
-	0	@ad<=20001221 and 'EEPROM' and 'HV' and 'LV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/30 16:26

-	21	@ad<=20001221 and 'flash memory' and 'HV' and 'LV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/03/30 16:26
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